

**isc Silicon NPN Power Transistor**
**2SC2522**
**DESCRIPTION**

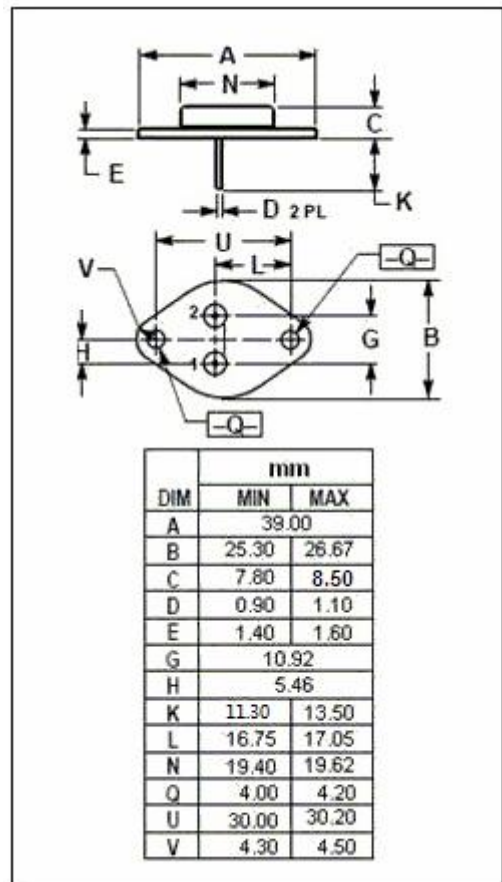
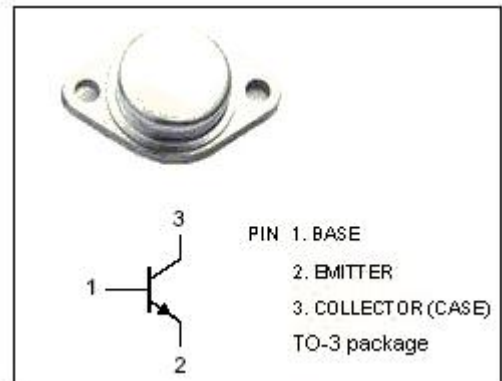
- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = 120V(\text{Min})$
- Fast Switching Speed
- Wide Area of Safe Operation
- Complement to Type 2SA1072
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- High frequency power amplifier
- Audio power amplifiers
- Switching regulators
- DC-DC converters

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	12	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	120	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor**
**2SC2522**
**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; R <sub>BE</sub> = ∞	120			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 50 μ A; I <sub>E</sub> = 0	120			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50 μ A ; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			1.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V			1.7	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V ; I <sub>E</sub> = 0			50	μ A
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 120V ;R <sub>BE</sub> = ∞			1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			50	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	60		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V	40			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		180		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V; f= 10MHz		80		MHz

**Switching Times**

t <sub>r</sub>	Rise Time			0.3		μ s
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 7.5A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.75A; R <sub>L</sub> = 4 Ω		1.3		μ s
t <sub>f</sub>	Fall Time			0.2		μ s

**NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.